

Suyog Gupta

List of Publications by Year in descending order

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16
papers

1,040
citations

840776

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h-index

1199594

12
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16
all docs

16
docs citations

16
times ranked

937
citing authors

#	ARTICLE	IF	CITATIONS
1	Dry-wet digital etching of Ge _{1-x} Sn _x . Applied Physics Letters, 2016, 108, .	3.3	12
2	Strained germanium-tin multiple quantum well microdisk resonators towards a light source on silicon. Proceedings of SPIE, 2015, , .	0.8	3
3	New materials for post-Si computing: Ge and GeSn devices. MRS Bulletin, 2014, 39, 678-686.	3.5	50
4	7-nm FinFET CMOS Design Enabled by Stress Engineering Using Si, Ge, and Sn. IEEE Transactions on Electron Devices, 2014, 61, 1222-1230.	3.0	79
5	Demonstration of a Ge/GeSn/Ge Quantum-Well Microdisk Resonator on Silicon: Enabling High-Quality Ge(Sn) Materials for Micro- and Nanophotonics. Nano Letters, 2014, 14, 37-43.	9.1	94
6	Highly Selective Dry Etching of Germanium over Germanium-Tin (Ge _{1-x} Sn _x): A Novel Route for Ge _{1-x} Sn _x Nanostructure Fabrication. Nano Letters, 2013, 13, 3783-3790.	9.1	83
7	A group IV solution for 7 nm FinFET CMOS: Stress engineering using Si, Ge and Sn. , 2013, , .		12
8	Material characterization of high Sn-content, compressively-strained GeSn epitaxial films after rapid thermal processing. Journal of Crystal Growth, 2013, 365, 29-34.	1.5	72
9	Approaches for a viable Germanium laser: Tensile strain, GeSn alloys, and n-type doping. , 2013, , .		4
10	Atomic layer deposition of Al ₂ O ₃ on germanium-tin (GeSn) and impact of wet chemical surface pre-treatment. Applied Physics Letters, 2013, 103, .	3.3	19
11	Theoretical Analysis of GeSn Alloys as a Gain Medium for a Si-Compatible Laser. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1502706-1502706.	2.9	77
12	Hole Mobility Enhancement in Compressively Strained $\{m_{Ge}_{0.93}\{m_{Sn}_{0.07}\}$ pMOSFETs. IEEE Electron Device Letters, 2013, 34, 831-833.	3.9	68
13	Achieving direct band gap in germanium through integration of Sn alloying and external strain. Journal of Applied Physics, 2013, 113, .	2.5	351
14	Low-Contact-Resistivity Nickel Germanide Contacts on n+Ge with Phosphorus/Antimony Co-Doping and Schottky Barrier Height Lowering. , 2012, , .		16
15	Performance Improvement of One-Transistor DRAM by Band Engineering. IEEE Electron Device Letters, 2012, 33, 29-31.	3.9	16
16	GeSn technology: Extending the Ge electronics roadmap. , 2011, , .		84